

WE CLAIM:

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1. A semiconductor device comprising:
an active area being provided with at least one MOS transistor; and
an insulating film defining said active area, wherein
said active area is set in a shape having a concave part in a shape along a
plan view,

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said active area is provided with:
an ordinary region, and
a depressed region having an edge portion being depressed beyond said
ordinary region due to presence of said concave part,
said at least one MOS transistor includes:
a first MOS transistor being formed on said depressed region, and
a second MOS transistor being formed on said ordinary region, and
15 ^a the length of a margin part of a first gate electrode constructing said first
MOS transistor is set to be larger than that of a margin part of a second gate
electrode constructing said second MOS transistor.

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2. The semiconductor device in accordance with claim 1, wherein
said concave part is formed on a corner portion of said active area, and
the length of said margin part of said first gate electrode is set at the total
of the length of said margin part of said second gate electrode and a length being
equal to a depression length in said concave part.

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3. The semiconductor device in accordance with claim 1, wherein

said concave part is formed on a corner portion of said active area, and the length of said margin part of said first gate electrode is set at the total of:

the length of said margin part of said second gate electrode, and

the length of a portion between said edge portion of said depressed region and an intersection between a virtual line being set to connect first and second convex corner portions of said active area in said concave part and said first gate electrode.

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- 10 4. The semiconductor device in accordance with claim 1, wherein said concave part is a dent part being formed on a portion of said active area other than said corner portion,
- said ordinary region is divided into first and second ordinary regions due to presence of said dent part,
- 15 an edge portion of said second ordinary region is on a position depressed beyond that of said first ordinary region, and
- the length of said margin part of said first gate electrode is set at the total of the length of said margin part of said second gate electrode and a length being equal to a depression length of said edge portions of said depressed region and said
- 20 second ordinary region.

5. The semiconductor device in accordance with claim 1, wherein said concave part is a dent part being formed on a portion of said active area other than said corner portion,

25 said ordinary region is divided into first and second ordinary regions due

to presence of said dent part,

an edge portion of said second ordinary region is on a position depressed beyond that of said first ordinary region, and

the length of said margin part of said first gate electrode is set at the total

5 of:

the length of said margin part of said second gate electrode, and

the length of a portion between said edge portion of said depressed region and an intersection between a virtual line being set to connect first and second convex corner portions of said active area in said concave part and said first gate electrode.

6. A semiconductor device comprising:

an active area being provided with at least one MOS transistor; and

an insulating film defining said active area, wherein

said active area is set in a shape having a concave part in a shape along a plan view,

said active area is provided with:

an ordinary region, and

a depressed region having an edge portion being depressed beyond said

20 ordinary region due to presence of said concave part,

said at least one MOS transistor includes:

a first MOS transistor being formed on said depressed region, and

a second MOS transistor being formed on said ordinary region, and

a margin part of a first gate electrode constructing said first MOS

25 transistor is set in a shape having a bent portion being bent at a prescribed angle to

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extend in a direction separating from said ordinary region.

7. The semiconductor device in accordance with claim 6, wherein
said concave part is formed on a corner portion of said active area,
said prescribed angle is 90° ,

said depressed region includes a first edge portion being perpendicular to
said first gate electrode and a second edge portion being parallel to said first gate
electrode,

said bent portion extends to be substantially in contact with or not in
contact with said first edge portion of said depressed region, and

the length of said bent portion is so set that its forward end portion
projects beyond said second edge portion of said depressed region by a distance
being equal to the length of a margin part of a second gate electrode constructing
said second MOS transistor.

8. The semiconductor device in accordance with claim 6, wherein
said concave part is formed on a corner portion of said active area,
said prescribed angle is 90° ,

said depressed region includes a first edge portion being perpendicular to
said first gate electrode and a second edge portion being parallel to said first gate
electrode,

said bent portion extends to be not in contact with said first edge portion
of said depressed region, and

the length of said bent portion is so set that its forward end portion
projects beyond an intersect position between a virtual line being set to connect

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first and second convex corner portions of said active area in said concave part and said first gate electrode by a distance being equal to the length of a margin part of a second gate electrode constructing said second MOS transistor.

5 9. The semiconductor device in accordance with claim 6, wherein
said concave part is formed on a corner portion of said active area,
said bent portion is bent about an intersect position between a virtual line
being set to connect first and second convex corner portions of said active area in
said concave part and said first gate electrode,
10 said prescribed angle is smaller than 90°, and
the length of said bent portion is so set that its forward end portion
projects beyond said intersect position by a distance being equal to the length of a
margin part of a second gate electrode constructing said second MOS transistor.

15 10. A semiconductor device comprising:
an active area being provided with at least one MOS transistor; and
an insulating film defining said active area, wherein
said active area is set in a shape having a concave part in a shape along a
plan view,
20 said active area is provided with:
an ordinary region, and
a depressed region having an edge portion being depressed beyond said
ordinary region due to presence of said concave part,
said at least one MOS transistor includes:
25 a plurality of MOS transistors being arranged on said depressed region

and electrically connected in parallel with each other, and

respective gate electrodes of said plurality of MOS transistors are arranged in parallel with each other and electrically connected in common,

so that margin parts of at least a gate electrode being located most
 5 approximately to said ordinary region and that adjacent to said gate electrode are connected with each other among said respective gate electrodes of said plurality of MOS transistors.

11. The semiconductor device in accordance with claim 10, wherein all
 10 margin parts of said respective gate electrodes of said plurality of MOS transistors are connected with each other.

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